# IMX6 DDR 测试工具使用

DDR 测试工具有两个版本,一个是 2.6,一个是 2.52 我一般用 2.52 版本。



TARGET MX6DL

DDR Der MX6DL

VDD\_AR MX6UL

MX6DQ

MX6SL MX6SX

MX7D



的,只是 IMX6DL 比 IMX6solo 多一个核。记住将开发板拨码开关拨到 00001100,这样才行。

ARM Speed

DDR CS

auto

Defau

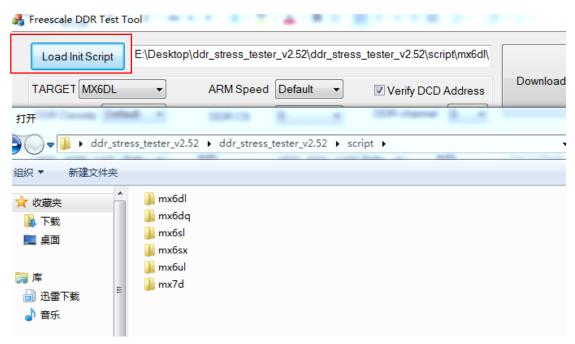
VDD\_

0

IMX6DL 芯片和 IMX6solo 芯

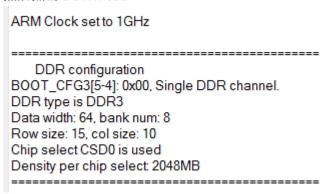
片都选择 MX6DL

因为 IMX6DL 和 IMX6solo 都是一样



点击 Load Init Scpript 选择脚本,如果使用的是 IMX6dl 或者 IMX6solo 那么就选择 MX6dl,如果是 IMX6Q 就选择 MXS6qd。

## 然后点击 DOWNload



这就是正常访问芯片了。

如果换了个 DDR 型号的芯片,就要对 DDR 芯片进行校正。



Write DQS5 delay: 46/256 CK Write DQS6 delay: 71/256 CK Write DQS7 delay: 49/256 CK

WARNING: write-leveling calibration value is greater than 1/8 CK.

Per the reference manual, WALAT must be set to 1 in the register MDMISC(0x021B0018).

This has been performed automatically.

However, in addition to updating the calibration values in your DDR initialization, it is also REQUIRED change the value of MDMISC in their DDR initialization as follows:

MMDC MDMISC (0x021b0018) = 0x00011740

Starting DQS gating calibration

进入 DDR 测试运行状态

最后会生成一个 DDROFFSET 报表

Starting Write calibration...

ABS OFFSET=0x000000000 result[00]=0x111111110 ABS OFFSET=0x04040404 result[01]=0x10101000 ABS OFFSET=0x08080808 result[02]=0x00100000 ABS OFFSET=0x0C0C0C0C result[03]=0x00000000 ABS\_OFFSET=0x10101010 result[04]=0x00000000 ABS\_OFFSET=0x14141414 result[05]=0x00000000 ABS\_OFFSET=0x18181818 result[06]=0x00000000 result[07]=0x000000000 ABS\_OFFSET=0x1C1C1C1C result[08]=0x00000000 ABS\_OFFSET=0x20202020 ABS OFFSET=0x24242424 result[09]=0x00000000 ABS OFFSET=0x28282828 result[0A]=0x000000000 ABS\_OFFSET=0x2C2C2C2C result[0B]=0x00000000 result[0C]=0x00000000 ABS\_OFFSET=0x3030303030

如果你没有换其他型号的内存,这里就已经结束操作了。

如果你换了其他型号的内存,那么在没有下载程序进开发板之前,就要先执行这个 DDR\_stream 软件, 生成上面这个 ABS\_OFFSET 列表。将列表里面的内容提取出来。 注意只需要修改 ABS OFFSET 列表里面的东西,其他不用动。

内核 uboot 文件中找到使用 ABS\_OFFSET 的代码,然后按照 DDR\_stream 生成的 OFFSET 对 uboot 里面的 offset 进行修改。然后从新编译 UBOOT,烧写进内核。

Write calibration

MPWRDLCTL PHY0 (0x021b0850) = 0x3832302E MPWRDLCTL PHY1 (0x021b4850) = 0x38363432

Success: DDR calibration completed!!!

这就是 DDR 测试成功。



这个是 DDR 压力测试。

# IMX6 DDR 内存大小修改指南

参考 MX6X\_3.14.28\_Uboot\_V1 版本资料

下载 yocto 环境, 在 yocto 的

root@ubuntu:/home/xiang/yocto/fsl-release-bsp/imx6qsabresd-fb/tmp/work/imx6qsabresd-poky-linux-gnueabi/u-boot-imx/2014.04-r0/git#

#### 这个目录下有 uboot 源码

按照 uboot 文档的要求

/home/vmuser/mx6x/fsl-release-bsp/imx6qsabresd-fb/tmp/work/imx6qsabresd-poky-linux-gnueabi/u-boot-imx/2014.04-r0/git/linux-g

export ARCH=arm

#### export

CROSS\_COMPILE=/opt/poky/1.7/sysroots/x86\_64-pokysdk-linux/usr/bin/arm-poky-linux-gnueabi/arm-poky-linux-gnueabi

make mx6qsabresd\_config-

Configuring for mx6qsabresd - Board: mx6sabresd, Options:

IMX\_CONFIG=board/freescale/imx/ddr/mx6q\_4x\_mt41j128.cfg,MX6Q,DEFAULT\_FDT\_FILE="imx 6q-sabresd.dtb",DDR MB=1024,SYS USE SPINOR

#### make

选择 IMX6 型号然后 make 就会生成 u-boot.imx 文件。这个文件就是给 MFG 下载进开发板 使用的 uboot 文件。

但是以上配置是官方的 CPU 为 IMX6Q, DDR 为美光的 1G 内存的下使用的 uboot。

# 我现在要修改 CPU 型号和内存大小:

CPU: IMX6solo

DDR:美光,但是大小为512M

mx6sabresd:IMX\_CONFIG=board/freescale/mx6sabresd/mx6solo\_4x\_mt41j128.cfg,MX6SOLO,DEFAULT\_FDT\_FILE="; mx6dl-sabresd.dtb",DDR\_MB=512,SYS\_USE\_SPINOR,SYS\_NOSMP="nosmp",ANDROID\_SUPPORT Fabio Estevam <a href="fabio.estevam@freescale.com">fabio.estevam@freescale.com</a>

2. If we change the size, need to modify the follow codes which define in

u-boot-2014.04-r0/boards.cfg as follows:

Active arm armv7 mx6 freescale mx6sabresd mx6qsabresd mx6qsabresd mx6qsabresd: IMX\_CONFIG=board/freescale/imx/ddr/mx6q\_4x\_mt41j128.cfg,MX6Q,DEFAULT\_FDT\_FILE="imx6q-sabresd: IMX\_CONFIG=board/freescale/imx/ddr/mx6q\_4x\_mt41j128.cfg,MX6Q,DEFAULT\_FDT\_FILE="imx6q-sabresd: Table 1024,SY8\_USE\_SPINOR Fabio Estevam <a href="fabio.estevam@freescale.com">fabio.estevam@freescale.com</a>

Change the size will change the DDR size, and after compile, it will set in the file (include\config.) as follows:

#define CONFIG\_IMX\_CONFIG\_ board/<u>freescale/imx/ddr/</u>mx6q\_4x\_mt41j128.cfg. #define CONFIG\_DDR\_MB 1024

按照上面的文档要求,在 uboot 目录下找到配置文件。先做 IMX6Q 的 uboot

root@ubuntu:/home/xiang/yocto/fsl-release-bsp/imx6qsabresd-fb/tmp/work/imx6qsabresd-poky-linux-gnueabi/u-boot-imx/2014.04-r0/git/include# vim config

# 打开该文件

```
1 /* Automatically generated - do not edit */
2 #define CONFIG_IMX_CONFIG board/freescale/mx6sabresd/mx6q_4x_mt41j128.cfg
3 #define CONFIG_DEFAULT_FDT_FILE "imx6q-sabresd.dtb"
5 #define CONFIG_DEFAULT_FDT_FILE "imx6q-sabresd.dtb"
5 #define CONFIG_SYS_USE_SPINOR 1
6 #define CONFIG_SYS_USE_SPINOR 1
7 #define CONFIG_SYS_ARCH "arm"
8 #define CONFIG_SYS_CPU "armv7"
9 #define CONFIG_SYS_BOARD "mx6sabresd
10 #define CONFIG_SYS_VENDOR "freescale"
11 #define CONFIG_SYS_SOC "mx6"
12 #define CONFIG_BOARDDIR board/freescale/mx6 ablesd
13 #include <config_end_defaults.h>
14 #include <config_end_defaults.h>
15 #include <config_end_defaults.h>
16 #include <config_fallbacks.h>
17 #include <config_fallbacks.h>
18 #include <config_uncmd_spl.h>
```

按照上面这个配置去先去 make mx6qsabresd\_config 指定编译哪一个 CPU 型号 make 一下,生成的 uboot 文件是给 IMX6Q 使用的。

CFGS board/freescale/imx/ddr/mx6q\_4x\_mt41j128.cfg.cfgtmp
MKIMAGE u-boot.imx
OBJCOPY u-boot.srec
bot@ubuntu:/home/xiang/yocto/fsl-release-bsp/imx6qsabresd-fb/tmp/work/imx6qsabresd-poky-linux-gnueabi/u-boot-imx/2014.04-r0/git#

将文件拷贝到 MFG 上面。记住要把 u-boot.imx 改成符合 MFG 格式的名字

<CMD state="Updater" type="push" body="send" file="files/u-boot-imx6q%
plus%%board% sd.imx" ifdev="MX6Q">Sending u-boot.bin</CMD>

根据 MFG 要求应该要改成这样的名字,但是不要加%号。这里有个问题? 实际的 MFG file 和 fireware 文件里面名字是这样的。

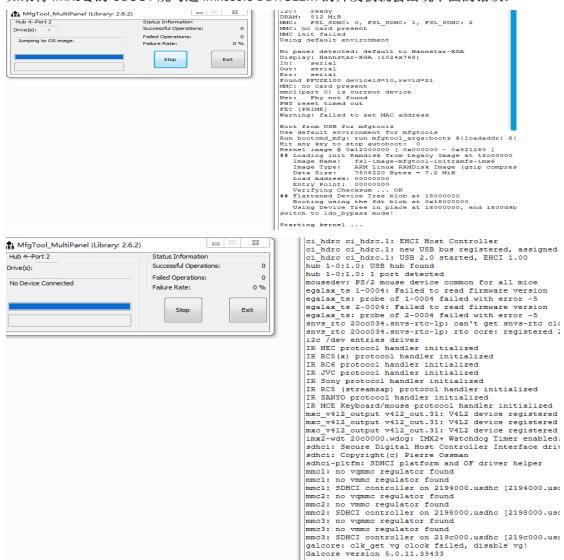
u-boot-imx6qsabresd\_sd.imx

证明了%%里面的内容是可以修改的。MFG 索引的应

该是%号之前和%之后的内容,两个%之间的内容可以修改。

然后下载程序进开发板。

正常运行,你会发现 IMX6DL 和 IMX6Q 开发板之间的 uboot 可以相互使用。如果将 IMX6Q 的 UBOOT 烧写进 imx6solo DDR 512M 的开发板就会出现下面的错误:



过了 jump OS 后就无法下载内核和文件系统了。

# 所以使用 IMX6solo DDR 大小为 512M 时。就需要对 config.h 文件进行修改了。

```
6 #define CONFIG_SYS_USE_SPINO
7 #define CONFIG_SYS_ARCH "ar
8 #define CONFIG_SYS_CPU "ar
                                                                                                    这里一定要
                                                                  这里用 imx6dl 的
                                                                   设备树,因为dl
                                                                                                    写成 CPU 的
                                                                 和 solo 是兼容的
sabresd
                                                                                                         型号
                                                      DDR 大小 512M
<mark>18</mark> #include
```

# 开始 make 编译

```
make[1]: *** No rule to make target `board/freescale/imx/ddr/mx6solo_4x_mt41j128.cfg', needed by `board/freescale/imx/ddr/mx6solo_4x_mt41j128.cfg.cf
tmp'. Stop.
make: *** [u-boot.imx] Error 2
root@ubuntu:/home/xiang/yocto/fsl-release-bsp/imx6qsabresd-fb/tmp/work/imx6qsabresd-poky-linux-gnueabi/u-boot-imx/2014.04-r0/git#
```

编译报错。因为你最先 make 配置的是 IMX6Q 的 CPU 型号,现在你要用 IMX6solo,那么你 就要重新指定 make 配置型号。

make mx6solosabresd config

这里一定要写成 mx6solosabresd config 而不是 mx6qsabresd\_confi 或者 mx6dlsabresd confi

# 否则在下载程序的时候会出现和上面一样的情况



```
执行 make mx6solosabresd config 之后,linux 终端会回显
oot@ubuntu:/home/xiang/yocto/fsl-release-bsp/imx6qsabresd-fb/tmp/work/imx6qsabresd-poky-linux-gnueabi/u-boot-imx/2014.04-r0/git# make mx6solosabres
onfiguring for mx6solosabresd - Board: mx6sabresd, Options: IMX_CONFIG=board/freescale/mx6sabresd/mx6solo_4x_mt41j128.cfg,MX6Sol0,DEFAULT_FDT_FILE=
mx6dl-sabresd.dtb",DDR_MB=512,S<u>YS_USE_SPINOR,SYS_NOSMP="nosmp"</u>
oot@ubuntu:/home/xiang/yocto/fsl-release-usp<del>/imx6qsabresd-fb/tmp/work/imx6qsabresd-poky-linux-gnueabi/u-boot-imx/2014.04-r0/git#</del>
然后你在 make
                                                                                                     这样就对了
 CFGS board/freescale/mx6sabresd/mx6solo_4x_mt41j128.cfg.cfgtmp
 MKIMAGE u-boot.imx
 OBJCOPY u-boot.srec
oot@ubuntu:/home/xiang/yocto/fsl-release-bsp/imx6qsabresd-fb/tmp/work/imx6qsabresd-poky-linux-gnueabi/u-boot-imx/2014.04-r0/git# cp u-boot.imx /mnt/
```

这样就是正常的 IMX6solo 单核, DDR 大小 512M 的配置, 下载进开发板就可以了。

# 用 IMX6solo 单核对 ddr 512M 内存大小进行调试

我们现在将主板换成 IMX6solo 单核,DDR 还是美光的,只是将 1G 改成了 512M,我们用 DDR Strem 软件对 512M 两片 128M\*16DDR 进行压力测试。



# 1. 我们先打开 I.MX6DQSDL DDR3 Script Aid V0.10 excel 格式的脚本文件

tkas Min (ns)	<b>ქ</b> 5	
System Information		
i.Mx Part	i.Mx6Q	Arik
Bus Width	64	
Density per chip select (Gb)	8	
Number of Chip Selects used	1	If only one CS is used, that must be CS
Total DRAM Density (Gb)	8	
DRAM Clock Freq (MHz)	528	
DRAM Clock Cycle Time (ns)	1.894	
Address Mirror (for CS1)	Disable	选择 regisert 配置
SI Configuration		
DRAM DSE Setting - DQ/DQM (ohm) 48		40ohm is used in FSL reference design.
Readme Register Configuration Re	ealView .inc DS-5.ds	Calibration (+)

## 2. 修改 execl 里面的参数

针对 i.MX6X 的 MMDC 配置如下:√

- Bus width=64(i.MX6S 仅支持 32 bit, i.MX6Q/D/DL 可以支持 64 或 32 bit)+
- Number of Chip Selects used=1(我们的 SDP 设计使用了一个 CS0 来连接 4片 DDR3)』
- DRAM Clock Freq(Mhz)=528(i.MX6Q/D 工作在 528Mhz, i.MX6DL/S 工作在 400Mhz)
- DRAM Clock Cycle Time(ns)=1.894(i.MX6Q/D=1/528Mhz=1.894ns, i.MX6DL/S=1/400Mhz=2.5ns)+/

注意 i.MX6X 的 MMDC 仅支持工作在 528Mhz 或 400Mhz, 所以虽然我们选择的 DDR3 可以工作在 800Mhz( DDR3-1600),所以我们在选择 DDR3 的时序参考时,我们使用 DDR3-1600 的时间 参数(单位 nS),而不是时钟周期参数(clock),因为时钟周期是按照 800MHz 来计算的,不正确。 4

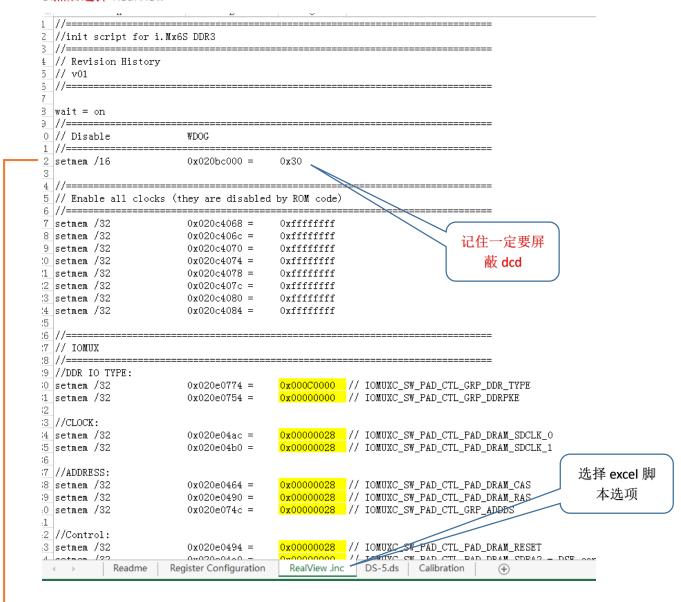
Memory part number: Micron Memory part number: MT41K128M16JT-125 Memory type: DDR3-1600 DRAM density (Gb) 2 DRAM Bus Width 16 Number of Banks 8 Number of ROW Addresses 14 Number of COLUMN Addresses 10 Page Size (K) 2 Self-Refresh Temperature (SRT) Normal 1RCD=RP=CL (ns) 13.75 tRC Min (ns) 48.75 tRAS Min (ns) 35  System Information i.Mx Part i.Mx6Q Bus Width 64 Density per chip select (Gb) 8 Number of Chip Selects used 1 DRAM Density (Gb) 8 DRAM Clock Freq (MHz) 528 DRAM Clock Selects Used 1 .894 Address Mirror (for CS1) Disable SI Configuration DRAM DSE Setting - DQ/DQM (ohm) 48 DRAM DSE Setting - DQDQ (ohm) 48 DRAM DSE Setting - DQS (ohm) 48 System ODT Setting (ohm) 60			
Memory part number: MT41K128M16JT-125  Memory type: DDR3-1600  DRAM density (Gb) DRAM Bus Width Number of Banks Number of ROW Addresses Number of COLUMN Addresses Page Size (K) Self-Refresh Temperature (SRT) NRCD=tRP=CL (ns) tRC Min (ns) System Information i.Mx Part Density per chip select (Gb) Number of Chip Selects used Total DRAM Density (Gb) DRAM Clock Cycle Time (ns) DRAM DSE Setting - DQ/DQM (ohm) DRAM DSE Setting - DQ/DQM (ohm) DRAM DSE Setting - DQ/DQM (ohm) DRAM DSE Setting - DQS (ohm) DRAM DSE Setting - DQS (ohm)  DRAM DSE Setting - DQS (ohm)  DRAM DSE Setting - DQS (ohm)  DRAM DSE Setting - DQS (ohm)  DRAM DSE Setting - DQS (ohm)  DRAM DSE Setting - DQS (ohm)  DRAM DSE Setting - DQS (ohm)  DRAM DSE Setting - DQS (ohm)  DRAM DSE Setting - DQS (ohm)  DRAM DSE Setting - DQS (ohm)  DRAM DSE Setting - DQS (ohm)  DRAM DSE Setting - DQS (ohm)  DRAM DSE Setting - DQS (ohm)			
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DRAM density (Gb)	Memory type:	DDR3-1600	
Windley of Banks Number of ROW Addresses Number of COLUMN Addresses 10 Page Size (K) Self-Refresh Temperature (SRT) Normal tRCD=tRP=CL (ns) tRAS Min (ns)  System Information i.Mx Part Bus Width Density per chip select (Gb) Number of Chip Selects used Total DRAM Density (Gb) DRAM Clock Freq (MHz) DRAM Clock Cycle Time (ns)  SI Configuration DRAM DSE Setting - DQ/DQM (ohm) DRAM DSE Setting - DQS (ohm)  Byskith Bus Width Bus I Am Was Bus William Bus Width Bus I Am Was Bus Was Bu	DRAM density (Gb)	2	
Number of ROW Addresses  Number of COLUMN Addresses  Page Size (K)  Self-Refresh Temperature (SRT)  tRCD=tRP=CL (ns)  tRC Min (ns)  System Information  i.Mx Part  Bus Width  Density per chip select (Gb)  Number of Chip Selects used  Total DRAM Density (Gb)  DRAM Clock Cycle Time (ns)  Address Mirror (for CS1)  DRAM DSE Setting - DQ/DQM (ohm)  DRAM DSE Setting - DQS (ohm)  Number of COLUMN Addresses  14  Normal  13.75  Normal  14.  Normal  148.75  Normal  13.75  tRC Min (ns)  35   ©为 IMX6S   及为 IMX6S  只支持 32  D为 IMX6S  只支持 32	DRAM Bus Width	16	
Number of COLUMN Addresses	Number of Banks	8	要除以/8
Page Size (K)   2     Self-Refresh Temperature (SRT)   Normal     tRCD=tRP=CL (ns)   13.75     tRC Min (ns)   48.75     tRAS Min (ns)   35     System Information   i.Mx 6Q     i.Mx Part   i.Mx6Q   改为 IMX6S     Bus Width   64     Density per chip select (Gb)   8     Number of Chip Selects used   1     DRAM DES Setting - DQ/DQM (ohm)   48     DRAM DSE Setting - DQS (ohm)	Number of ROW Addresses	14	
Self-Refresh Temperature (SRT)	Number of COLUMN Addresses	10	
### RCD=tRP=CL (ns)	Page Size (K)	2	
tRC Min (ns)  tRAS Min (ns)  System Information  i.Mx Part  Bus Width  Density per chip select (Gb)  Number of Chip Selects used  Total DRAM Density (Gb)  DRAM Clock Freq (MHz)  DRAM Clock Cycle Time (ns)  Address Mirror (for CS1)  DRAM DSE Setting - DQ/DQM (ohm)  DRAM DSE Setting - CK (ohm)  DRAM DSE Setting - DQS (ohm)  48  DRAM DSE Setting - DQS (ohm)  DRAM DSE Setting - DQS (ohm)	Self-Refresh Temperature (SRT)	Normal	1
System Information  i.Mx Part i.Mx6Q  Bus Width Density per chip select (Gb) Number of Chip Selects used Total DRAM Density (Gb) DRAM Clock Freq (MHz) DRAM Clock Cycle Time (ns) Address Mirror (for CS1) DRAM DSE Setting - DQ/DQM (ohm) DRAM DSE Setting - ADDR/CMD/CTL (ohm) DRAM DSE Setting - DQS (ohm)  ti.Mx6Q DX	tRCD=tRP=CL (ns)	13.75	
System Information i.Mx Part i.Mx6Q  Bus Width  Density per chip select (Gb)  Number of Chip Selects used  Total DRAM Density (Gb)  DRAM Clock Freq (MHz)  DRAM Clock Cycle Time (ns)  Address Mirror (for CS1)  DRAM DSE Setting - DQ/DQM (ohm)  DRAM DSE Setting - CK (ohm)  DRAM DSE Setting - DQS (ohm)  Objective in.Mx6Q  By IMX6S  Expression  AB  DRAM DSE Setting - CK (ohm)  By IMX6S	tRC Min (ns)	48.75	
i.Mx Part i.Mx6Q 改为 IMX6S  Bus Width 64  Density per chip select (Gb) 8  Number of Chip Selects used 1  DRAM Clock Freq (MHz) 528  DRAM Clock Cycle Time (ns) 1.894  Address Mirror (for CS1) Disable  SI Configuration  DRAM DSE Setting - DQ/DQM (ohm) 48  DRAM DSE Setting - ADDR/CMD/CTL (ohm) 48  DRAM DSE Setting - CK (ohm) 48  DRAM DSE Setting - DQS (ohm) 48	tRAS Min (ns)	35	
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Number of Chip Selects used  Total DRAM Density (Gb)  DRAM Clock Freq (MHz)  DRAM Clock Cycle Time (ns)  Address Mirror (for CS1)  DISABLE  DRAM DSE Setting - DQ/DQM (ohm)  DRAM DSE Setting - ADDR/CMD/CTL (ohm)  DRAM DSE Setting - CK (ohm)  DRAM DSE Setting - DQS (ohm)	Bus Width	64	
Total DRAM Density (Gb) 8 只支持 32 DRAM Clock Freq (MHz) 528 DRAM Clock Cycle Time (ns) 1.894 Address Mirror (for CS1) Disable BI Configuration DRAM DSE Setting - DQ/DQM (ohm) 48 DRAM DSE Setting - CK (ohm) 48 DRAM DSE Setting - DQS (ohm) 48	Density per chip select (Gb)	8	
DRAM Clock Freq (MHz)       528         DRAM Clock Cycle Time (ns)       1.894         Address Mirror (for CS1)       Disable         SI Configuration       因为 IMX6S 只 支持 32 位         DRAM DSE Setting - DQ/DQM (ohm)       48         DRAM DSE Setting - CK (ohm)       48         DRAM DSE Setting - DQS (ohm)       48	Number of Chip Selects used		因为 IMX6S
DRAM Clock Freq (MHz)       528         DRAM Clock Cycle Time (ns)       1.894         Address Mirror (for CS1)       Disable         SI Configuration       因为 IMX6S 只         DRAM DSE Setting - DQ/DQM (ohm)       48         DRAM DSE Setting - ADDR/CMD/CTL (ohm)       48         DRAM DSE Setting - CK (ohm)       48         DRAM DSE Setting - DQS (ohm)       48		8	只支持 32
Address Mirror (for CS1)	DRAM Clock Freq (MHz)	528	
SI Configuration  DRAM DSE Setting - DQ/DQM (ohm)  DRAM DSE Setting - ADDR/CMD/CTL (ohm)  DRAM DSE Setting - CK (ohm)  DRAM DSE Setting - DQS (ohm)  48  DRAM DSE Setting - DQS (ohm)	DRAM Clock Cycle Time (ns)	1.894	
DRAM DSE Setting - DQ/DQM (ohm) 48 支持 32 位 DRAM DSE Setting - ADDR/CMD/CTL (ohm) 48 DRAM DSE Setting - CK (ohm) 48 DRAM DSE Setting - DQS (ohm) 48		Disable	田光山水の日
DRAM DSE Setting - ADDR/CMD/CTL (ohm)         48           DRAM DSE Setting - CK (ohm)         48           DRAM DSE Setting - DQS (ohm)         48	SI Configuration		
DRAM DSE Setting - CK (ohm) 48  DRAM DSE Setting - DQS (ohm) 48			支持 32 位
DRAM DSE Setting - DQS (ohm) 48			
		48	
System ODT Setting (ohm) 60		48	
	System ODT Setting (ohm)	60	]

# 修改后就是这样

Device Information	
Manufacturer:	Micron
Memory part number:	MT41K128M16JT-125
Memory type:	DDR3-1600
DRAM density (Gb)	4
DRAM Bus Width	16
Number of Banks	8
Number of ROW Addresses	14
Number of COLUMN Addresses	10
Page Size (K)	2
Self-Refresh Temperature (SRT)	Normal
tRCD=tRP=CL (ns)	13.75
tRC Min (ns)	48.75
tRAS Min (ns)	35
System Information	
i.Mx Part	i.Mx6S
Bus Width	32
Density per chip select (Gb)	4
Number of Chip Selects used	1
Total DRAM Density (Gb)	4
DRAM Clock Freq (MHz)	400
DRAM Clock Cycle Time (ns)	2.5
Address Mirror (for CS1)	Disable
SI Configuration	
DRAM DSE Setting - DQ/DQM (ohm)	48
DRAM DSE Setting - ADDR/CMD/CTL (ohm)	48
DRAM DSE Setting - CK (ohm)	48
DRAM DSE Setting - DQS (ohm)	48
System ODT Setting (ohm)	60

这样就修改完毕了

## 3.然后选择 RealView



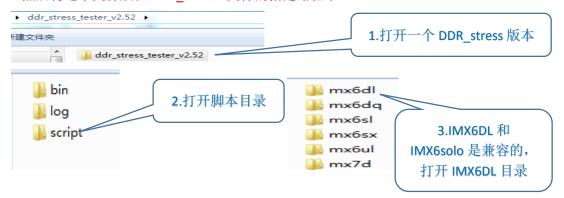
 →// setmem /16
 0x020bc000 =
 0x30 //注掉此项, DCD 不可以访问此地址√

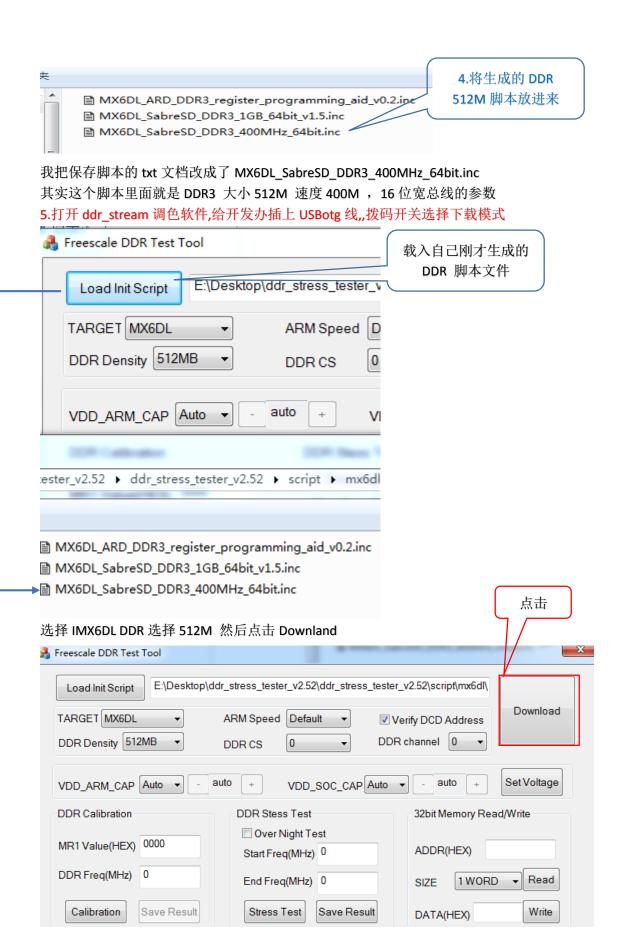
这个文件就是根据前面 register Configuration 选项自动设置的脚本文件。

然后我们就可以从 Realview.inc 页中获得 DDR3 的初始化设置,拷贝出来保存在一下 txt 文件中,然后改名为:"MX6QD\_SabreSD\_DDR3\_528MHz\_64bit.inc"。↩

这个名字随便改,只要保证后缀是.inc 就可以了。

4.然后将这个文件放在 DDR stream 文件的指定路径下





成功载入脚本就是下面这样

Boot Configuration SRC\_SBMR1(0x020d8004) = 0x00010030 SRC\_SBMR2(0x020d801c) = 0x32000001

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#### ARM Clock set to 1GHz

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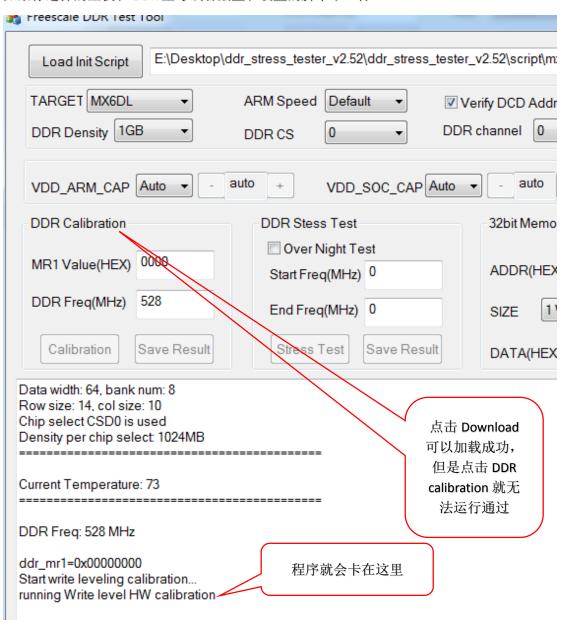
DDR configuration

BOOT\_CFG3[5-4]: 0x00, Single DDR channel.

DDR type is DDR3

Data width: 32, bank num: 8 Row size: 14, col size: 10 Chip select CSD0 is used Density per chip select: 512MB

如果你选择的主板和 DDR 型号或者数量和设置的脚本不一样



如果你选择的脚本和主板 CPU 的信号和 DDR 是匹配的

ddr mr1=0x00000000

Start write leveling calibration...

running Write level HW calibration

Write leveling calibration completed, update the following registers in your initialization script

MMDC\_MPWLDECTRL0 ch0 (0x021b080c) = 0x0043004A

MMDC\_MPWLDECTRL1 ch0 (0x021b0810) = 0x00350037

Write DQS delay result:

Write DQS0 delay: 74/256 CK

Write DQS1 delay: 67/256 CK

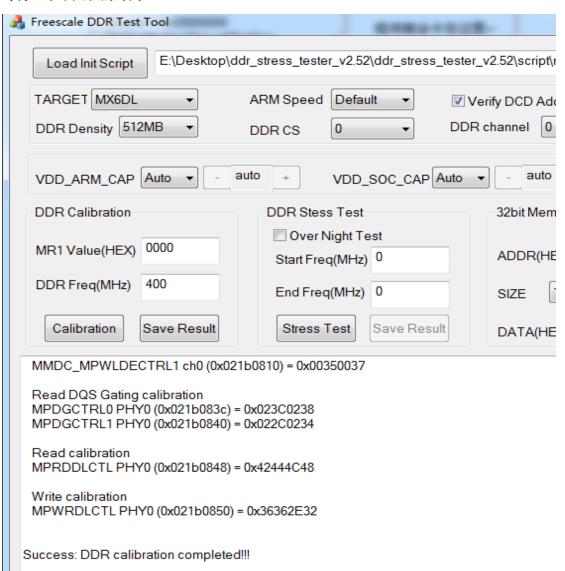
Write DQS2 delay: 55/256 CK

Write DQS3 delay: 53/256 CK

# Starting DQS gating calibration

. . . . . .

在进行 DDR calibration 也就是 DDR 校准的时候,会成功执行到 Starting DQS 信号测试 等待一个不太长的时间



DDR 成功校准

# 6.然后对 DDR 进行压力测试

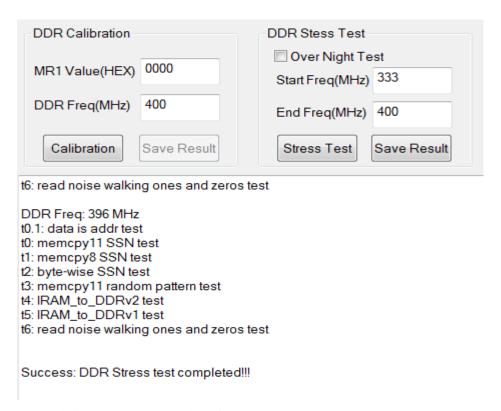
🔒 Freescale DDR Test Tool		
Load Init Script E:\Desktop\dd	r_stress_tester_v2.52\ddr_stress_tester_v	v2.52∖s
TARGET MX6DL ▼	ARM Speed Default ▼ Ve	rify DCI
DDR Density 512MB ▼	DDR CS 0 → DDR	channe
VDD_ARM_CAP Auto ▼ - au	uto + VDD_SOC_CAP Auto ▼	] [
DDR Calibration DDR 校准测试	DDR Stess Test DDR 压力测试	-32bit
MR1 Value(HEX) 0000	Over Night Test Start Freq(MHz)	ADD
DDR Freq(MIAz) 400	End Freq(MHz) 0	SIZE
Calibration Save Result	Stress Test Save Result	DAT

DDR 压力测试频率标准

束频率。此频率必须在 135 MHz 至 672 MHz 的范围内。由于 tCK(AVG).MIN = 3 ns 限制了 DLL 何时启用且 "Aid"的脚本仅支持 DLL 启用,因此 DDR3 的工作频点设置应高于 333 MHz。如

DDR Calibration	DDR Stess Test			
MR1 Value(HEX) 0000	Over Night Test			
	Start Freq(MHz) 333			
DDR Freq(MHz) 400	End Freq(MHz) 400			
Calibration Save Result	Stress Test Save Result			
DDR Freq: 327 MHz t0.1: data is addr test t0: memcpy11 SSN test t1: memcpy8 SSN test t2: byte-wise SSN test t3: memcpy11 random pattern test t4: IRAM_to_DDRv2 test t5: IRAM_to_DDRv1 test t6: read noise walking ones and zeros test  DDR Freq: 339 MHz t0.1: data is addr test t0: memcpy11 SSN test t1: memcpy8 SSN test				

这就是 DDR 压力测试



DDR 3 内存 333M~400M 速率压力测试成功。 如果我重启主板,先进行压力测试可以吗?

DDR Calibration	DDR Stess Test
MR1 Value(HEX) 0000	Over Night Test Start Freq(MHz) 333
DDR Freq(MHz) 400	End Freq(MHz) 400
Calibration Save Result	Stress Test Save Result
DDR Stress Test Iteration 1 Current Temperature: 76  DDR Freq: 327 MHz t0.1: data is addr test Address of failure: 0x10000080 Data was: 0x10000000 But pattern should match address Error: failed to run stress test!!!	

这就是重启主板后先 Download 脚本,然后不经过 DDR 校准,直接进入 DDR 压力测试,发送错误。所以必须先进行 DDR 校准,然后才能进行 DDR 压力测试,顺序不能乱。